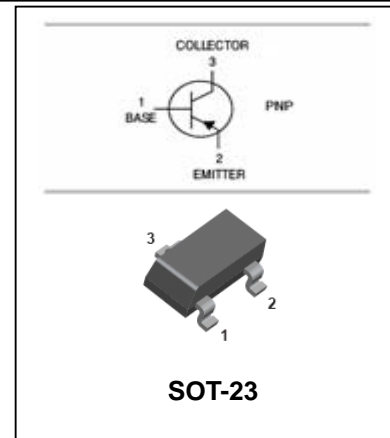


Silicon Epitaxial Planar Transistor

2SA1162

FEATURES

- Low noise: NF=1dB(Typ), 10dB(Max).
- Complementary to 2SC2712.
- Small package.



APPLICATIONS

- General purpose application.

ORDERING INFORMATION

Type No.	Marking	Package Code
2SA1162	SO/SY/SG	SOT-23

MAXIMUM RATING @ Ta=25°C unless otherwise specified

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-50	V
V_{CEO}	Collector-Emitter Voltage	-50	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-150	mA
P_C	Collector Dissipation	150	mW
T_j, T_{stg}	Junction and Storage Temperature	-55~125	°C

Silicon Epitaxial Planar Transistor

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ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-100\mu A, I_E=0$	-50			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1mA, I_B=0$	-50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-100\mu A, I_C=0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-50V, I_E=0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-5V, I_C=0$			-0.1	μA
DC current gain	h_{FE}	$V_{CE}=-6V, I_C=-2mA$	70		400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-100mA, I_B=-10mA$		-0.1	-0.3	V
Transition frequency	f_T	$V_{CE}=-10V, I_C=-1mA$	80			MHz
Collector output capacitance	C_{ob}	$V_{CB}=-10V, I_E=0, f=1MHz$		4	7	pF
Noise figure	NF	$V_{CE}=-6V, I_C=0.1mA, f=1MHz, R_g=10k\Omega$		1.0	10	dB

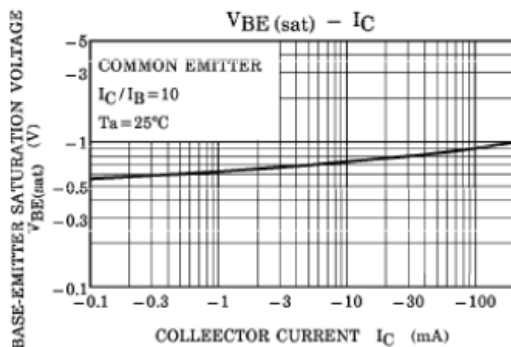
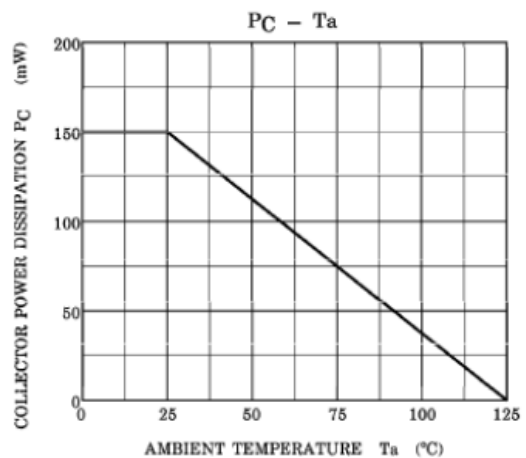
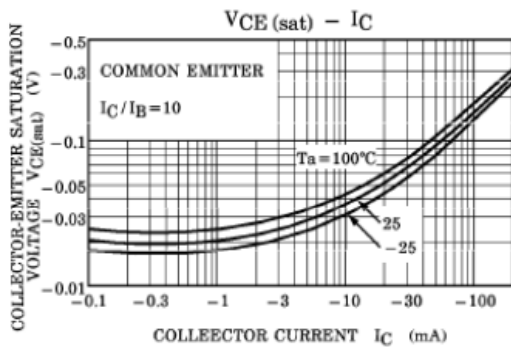
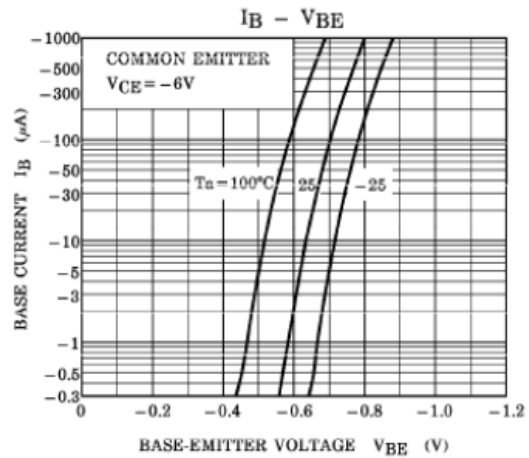
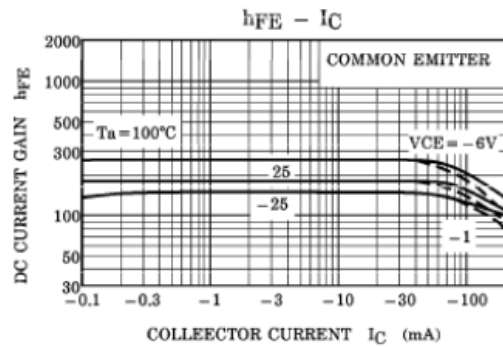
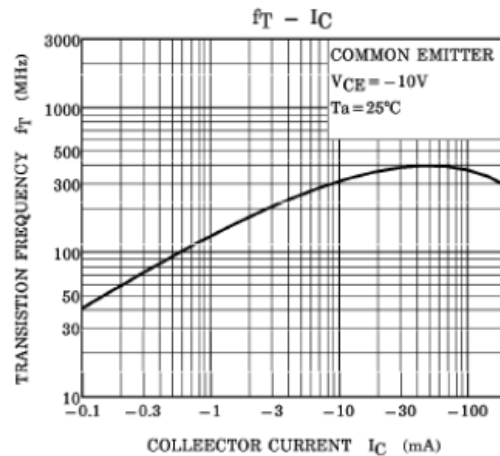
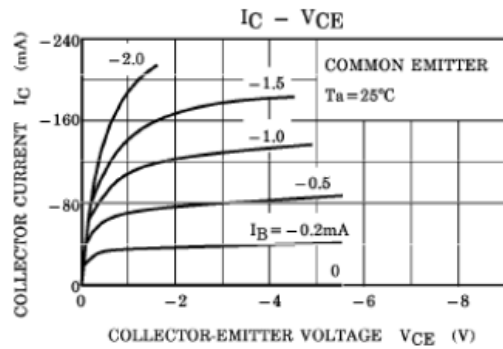
CLASSIFICATION OF $h_{FE(1)}$

Rank	O	Y	G
Range	70-140	120-240	200-400

Silicon Epitaxial Planar Transistor

2SA1162

TYPICAL CHARACTERISTICS @ $T_a=25^\circ\text{C}$ unless otherwise specified



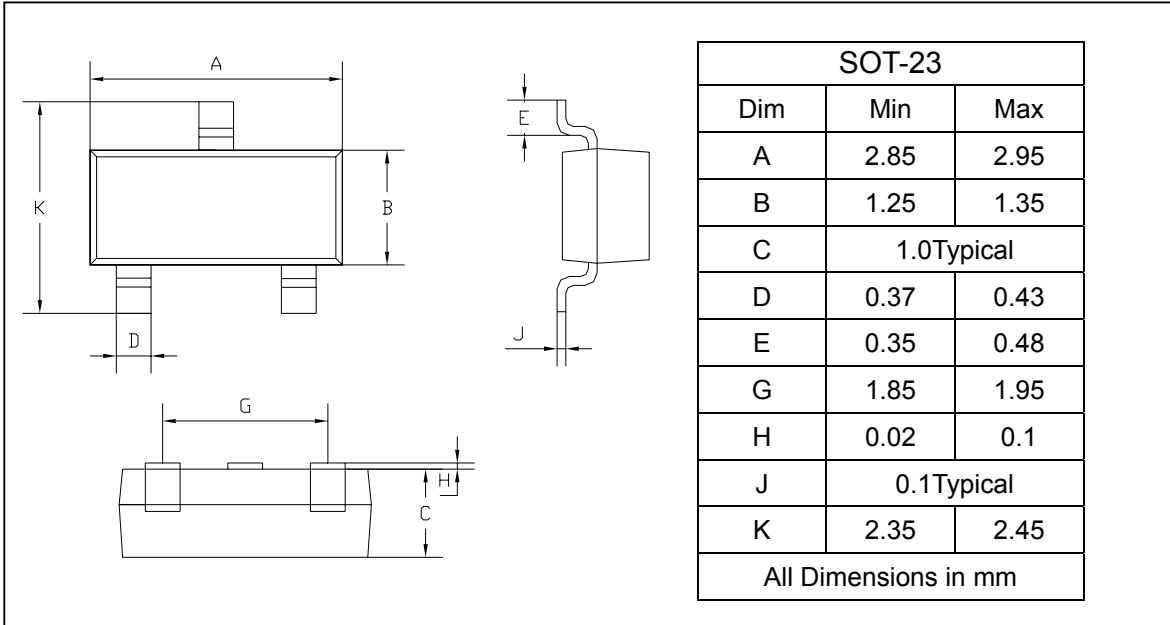
Silicon Epitaxial Planar Transistor

2SA1162

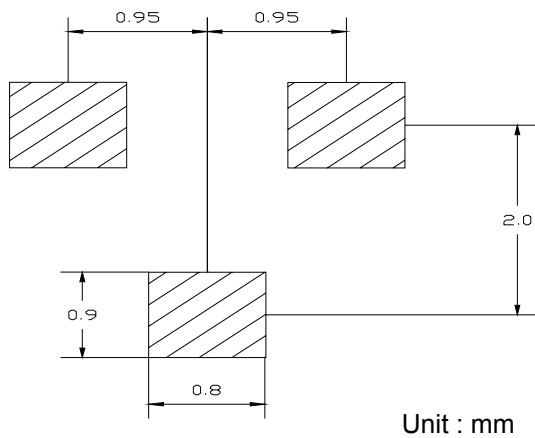
PACKAGE OUTLINE

Plastic surface mounted package

SOT-23



SOLDERING FOOTPRINT



PACKAGE INFORMATION

Device	Package	Shipping
2SA1162	SOT-23	3000/Tape&Reel